

Disclosed is a polymer for use in a chemically amplified resist, a resist composition including such a polymer is suitable for use in a chemically amplified resist, which is sensitive to KrF or ArF excimer laser and forms a photoresist pattern having low dependence on and good adhesion to substrate, high transparency in the wavelength range of the above radiation, strong resistance to dry etching, and excellencies in sensitivity, resolution and developability. The resist composition can have a stronger etching resistance with a maximized content of unsaturated aliphatic ring in the polymer and a reduced edge roughness of the photoresist pattern with an alkoxyalkyl acrylate monomer employed.

REMARKS

The specification has been amended to correct spelling and typographical errors. In particular, the misspelling of isobronyl methacrylate as "isobornyl methacrylate" has been corrected. The reference to the solvent γ -butyrolacton has been corrected by removing the "v" and replacing it with " γ ". In addition, reference to KrF and ArF excimer lasers has been amended to more clearly point out the suitability of using those lasers in the present invention. No new matter has been added

Respectfully submitted,

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